

# Monika Bhattacharya

## List of Publications by Year in descending order

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17  
papers

98  
citations

1684188  
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1474206  
9  
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17  
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docs citations

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times ranked

59  
citing authors

#	ARTICLE	IF	CITATIONS
1	Sheet carrier concentration and current-voltage analysis of Al <sub>0.15</sub> Ga <sub>0.85</sub> N/GaN/Al <sub>0.15</sub> Ga <sub>0.85</sub> N double heterostructure hemt incorporating the effect of traps. Microsystem Technologies, 2022, 28, 665-674.	2.0	8
2	Extraction of admittance parameters of symmetrically doped AlGaN/GaN/AlGaN DH-HEMT for microwave frequency applications. Microsystem Technologies, 2021, 27, 4065-4072.	2.0	4
3	Analysis of Al <sub>0.15</sub> Ga <sub>0.85</sub> N/GaN/Al <sub>0.15</sub> Ga <sub>0.85</sub> N DH-HEMT for RF and Microwave Frequency Applications. Semiconductors, 2019, 53, 1784-1791.	0.5	5
4	Impact of Donor Layer Thickness, Doping Concentration and Gate-Width on Gate-Capacitance of AlGaN/GaN Single and Double Heterostructure HEMT for Microwave Frequency Applications. , 2018, , .		1
5	RF Performance comparison of Dual Material Gate (DMG) and Conventional AlGaN/GaN High Electron Mobility Transistor. , 2018, , .		0
6	Impact of donor-layer doping & thickness, gate-length and temperature on potential and electron concentration in AlGaN/GaN Double-Heterostructure and Single-Heterostructure HEMT. , 2018, , .		0
7	Polarization dependent charge control model for microwave performance assessment of AlGaN/GaN/AlGaN double heterostructure HEMTs. Journal of Computational Electronics, 2018, 17, 1229-1240.	2.5	12
8	Influence of gate leakage current induced shot noise on the Minimum Noise Figure of InAlAs/InGaAs double-gate HEMT. Superlattices and Microstructures, 2017, 109, 13-22.	3.1	3
9	Sheet carrier concentration and threshold voltage modeling of asymmetrically doped AlGaN/GaN/AlGaN double heterostructure HEMT. , 2017, , .		7
10	Impact of Temperature and Indium Composition in the Channel on the Microwave Performance of Single-Gate and Double-Gate InAlAs/InGaAs HEMT. IEEE Nanotechnology Magazine, 2013, 12, 965-970.	2.0	4
11	Temperature-Dependent Analytical Model for Microwave and Noise Performance Characterization of $\text{In}_{0.52}\text{Al}_{0.48}\text{As}/\text{In}_m\text{Ga}_{1-m}\text{As}$ ( $0.53 \leq m \leq 1$ ) Tj ETQq1 1.0.7843 14 rgBT / Ov	1.0	4
12	A comprehensive charge control based analysis of the effect of donor-layer doping and donor-layer thickness on the P, R and C noise coefficients of a symmetric tied-gate InAlAs/InGaAs DG-HEMT. Proceedings of SPIE, 2012, , .	0.8	0
13	Impact of noise temperature constant and diffusion coefficient on the minimum noise figure and minimum noise temperature of InAlAs/InGaAs DGHEMT. , 2012, , .		0
14	An Accurate Charge-Control-Based Approach for Noise Performance Assessment of a Symmetric Tied-Gate InAlAs/InGaAs DG-HEMT. IEEE Transactions on Electron Devices, 2012, 59, 1644-1652.	3.0	17
15	Scattering parameter based modeling and simulation of symmetric tied-gate InAlAs/InGaAs DG-HEMT for millimeter-wave applications. Solid-State Electronics, 2011, 63, 149-153.	1.4	12
16	Impact of doping concentration and donor-layer thickness on the dc characterization of symmetric double-gate and single-gate InAlAs/InGaAs/InP HEMT for nanometer gate dimension-A comparison. , 2010, , .		9
17	Applicability of Field Plate in Double Channel GaN HEMT for Radio-Frequency and Power-Electronic Applications. Silicon, 0, , 1.	3.3	8